

SB10-09P

Schottky Barrier Diode

90V, 1A Rectifier

Applications

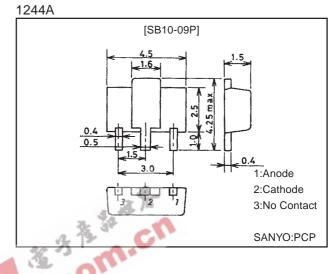
• High frequency rectification (switching regulators, converters, choppers).

Features

- · Low forward voltage (V_F max=0.7V).
- Fast reverse recovery time (trr max=20ns).
- · Low switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

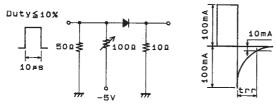
| | - | | | |
|--|------------------|-------------------------|-------------|------|
| Parameter | Symbol | Conditions | Ratings | Unit |
| Repetitive Peak Reverse Voltage | V _{RRM} | | 90 | V |
| Nonrepetitive Peak Reverse Surge Voltage | VRSM | | 95 | V |
| Average Output Current | 10 | | 1 | A |
| Surge Forward Current | IFSM | 50Hz sine wave, 1 cycle | 5 | A |
| Junction Temperature | Tj | | -55 to +125 | °C |
| Storage Temperature | Tstg | | –55 to +125 | °C |

Electrical Characteristics at Ta = 25°C

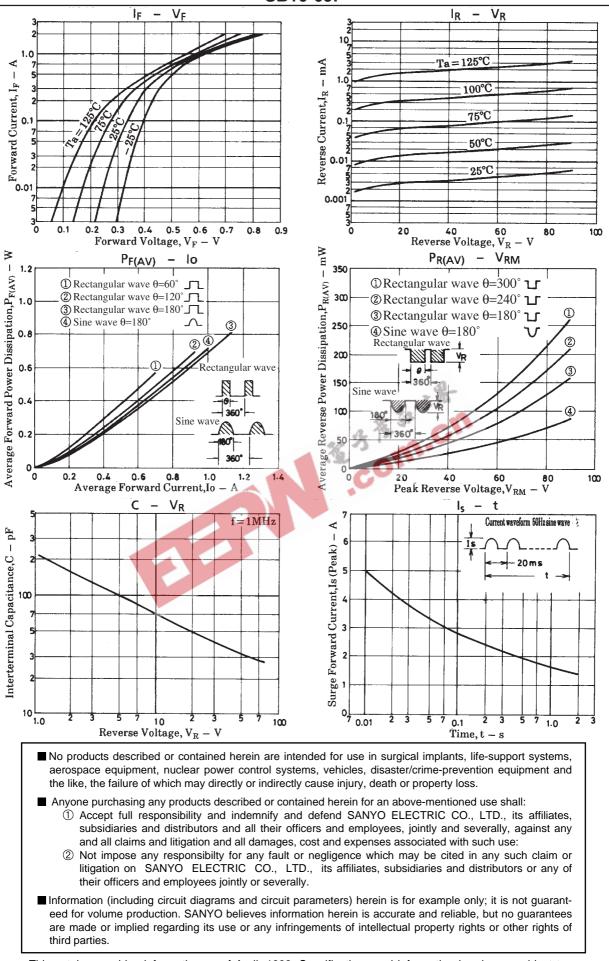
| Parameter | | Conditons | Ratings | | | Unit |
|---------------------------|----------------|--|---------|-----|-----|------|
| | Symbol | | min | typ | max | |
| Reverse Voltage | VR | I _R =1mA | 90 | | | V |
| Forward Voltage | ٧ _F | I _F =1A | | | 0.7 | V |
| Reverse Current | IR | V _R =45V | | | 200 | μA |
| Interterminal Capacitance | С | V _R =10V, f=1MHz | | 70 | | pF |
| Reverse Recovery Time | trr | I _F =I _R =100mA, See specifaied Test Circuit | | | 20 | ns |
| Thermal Resistance | Rthj-a (1) | | | 280 | | °C/W |
| | Rthj-a (2) | Mounted on 250mm ² ×0.8mm ceramic board | | 100 | | °C/W |

Marking:SJ

trr Test Circuit



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This catalog provides information as of April, 1998. Specifications and information herein are subject to change without notice.